

MANUFACTURE OF SEMICONDUCTOR DEVICE

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Abstract

PURPOSE: To form narrowly a scribe line region to contrive high density integration of a semiconductor integrated circuit element by providing an laser resistant protective film on a transparent insulator.

CONSTITUTION: An laser resistant protective film 7 is positioned at both poitions of a scribe line region 1, and is formed so as to be positioned between a semiconductor integrated circuit element 2 and a sapphire substrate 3. And, a laser beam is applied from the rear surface of the sapphivre substrate 3 opposite to the surface where the semiconductor integrated circuit element 2 is formed along the scribe line region 1, and the substrate 3 is scribed from the rear surface to form a groove part 4. And, the thin substrate 3 between the groove part 4 and the scribe line region 1 is bent and cut to divide into a plurality of chips.

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